

600V SiC Schottky Diode

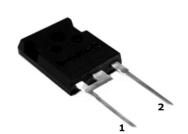


GDP24P060B

VDC 600 V Q_C 50 nC I_F (V_F=1.5V) 24 A

Amp+™ Features

- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Fast, temperature-independent switching



Amp+™ Benefits

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices with thermal stability

Amp+[™] Applications

- Motor drives
- Switch mode power supplies
- Power factor correction
- Diode snubber

Part #	Package	Marking		
GDP24P060B	TO-247-2	GDP24P060		



Maximum Rating	Symbol	Conditions	Value	Unit	
Continuous forward current		T _C =25 °C, T _j =175 °C	46		
	I _F	T _C =125 °C, T _j =175 °C	25		
		T _C =150 °C, T _j =175 °C	17		
Surge non-repetitive forward current sine halfwave	1	$T_C=25$ °C, $t_p=8.3$ ms	192	Α	
	I _{F,SM}	T_{C} =150 °C, t_{p} =8.3 ms	120		
Non-repetitive peak forward current	I _{F,max}	T _C =25 °C, t _p =10 μs	480		
i^2t value	∫i²dt	$T_C=25$ °C, $t_p=8.3$ ms	153	A ² s	
	JI at	T_C =150 °C, t_p =8.3 ms	60		
Repetitive peak reverse voltage	V_{RRM}	T _j =25 °C	600	V	
Diode dv/dt ruggedness	dv/dt	Turn-on slew rate, repetitive	50	V/ns	
Power dissipation	P _{tot}	T _C =25 °C	195	W	
Operating & storage temperature	T _C , T _{storage}	Continuous	-55135	°C	
Soldering temperature	T _{solder}	Wave soldering leads	260	°C	
Mounting torque		M3 Screw	1	N-m	

Electrical Characteristics, at T_j=25 °C, unless otherwise specified

Static Characteristics	Symbol	Conditions		Values		
			min.	typ.	max.	Unit
DC blocking voltage	V_{DC}		600	-	-	
Diode forward voltage	V _F	I _F =24A, T _j =25 °C	-	1.5	1.7	V
		I _F =24A, T _j =175 °C	-	2.5	2.8	
Reverse current	I _R	V _R =600V, T _j =25 °C	-	6.6	100	μΑ
		V _R =600V, T _j =175 °C	-	2687	-	

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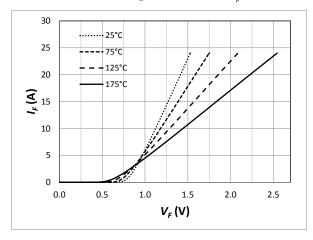
Parameter	Symbol	Conditions	Values			Unit
	Symbol		min.	typ.	max.	Unit
AC Characteristics						
Total capacitive charge	Q _{rr}	V _R =600V, T _j =27 °C	-	50	-	nC
Switching time	t _C	di_F/dt =200 A/ μ s T $_j$ =150 °C	-	-	<10	ns
Total capacitance		V _R =1 V, f=1 MHz	-	973	-	
	С	V _R =300V, f=1 MHz	-	86	-	pF
		V _R =600V, f=1 MHz	-	83	-	

Thermal Characteristics

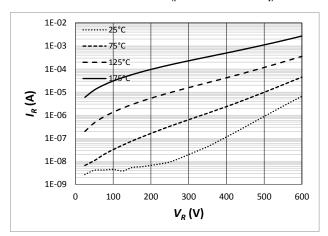
Thermal resistance, junction-case	R_{thJC}	Package (flange) mount	-	0.77	-	°C/W

Typical Performance

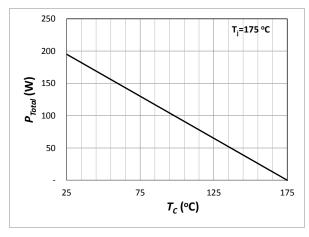
Forward Characteristics (parameterized on T_i)



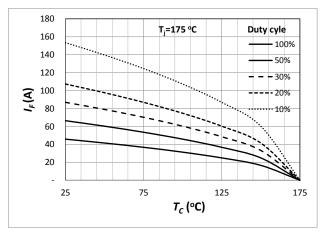
Reverse Characteristics (parameterized on Tj)



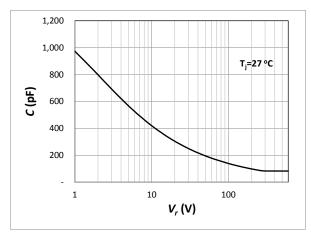
Power Derating



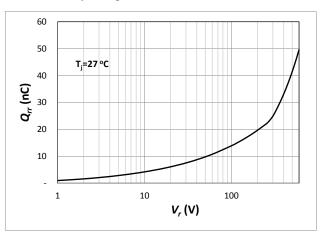
Current Derating



Capacitance

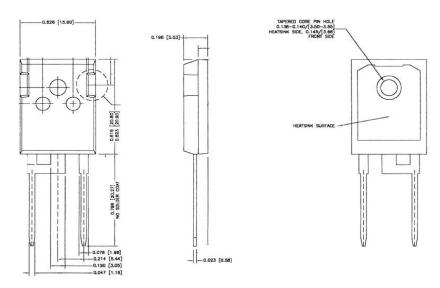


Recovery Charge



Package Dimensions

Package TO-247-2



Note RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.gptechgroup.com.

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemi- cal Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at GPTG Headquarters in Lake Forest, California to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication

Global Power Technologies Group Inc., Reserves the right to make changes to the product specifications and data in this document without notice.